



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

DSK32W-DSK310W

SOD-123FL Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SOD-123FL



■Maximum Rating 最大额定值

($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	DSK 32W	DSK 33W	DSK 34W	DSK 35W	DSK 36W	DSK 37W	DSK 38W	DSK 39W	DSK 310W	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	50	60	70	80	90	100	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	50	60	70	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	35	42	49	56	63	70	V
Forward Rectified Current 正向整流电流	I_F	3								A	
Peak Surge Current 峰值浪涌电流	I_{FSM}	80								A	
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	10								°C/W	
Junction/Storage Temperature 结温/储藏温度	T_J, T_{stg}	-50 to +150°C								°C	

■Electrical Characteristics 电特性

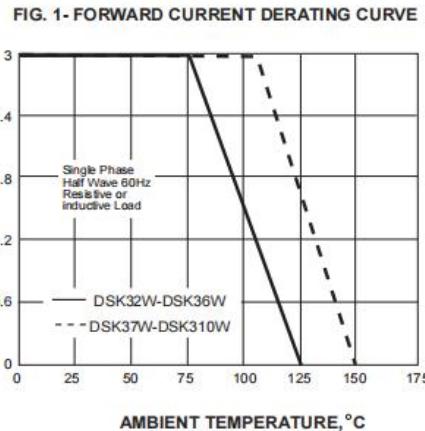
($T_A=25^\circ\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	DSK32W	DSK33W- DSK34W	DSK35W- DSK36W	DSK37W- DSK310W	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.52	0.55	0.70	0.85	V	$I_F=3\text{A}$
Reverse Current 反向电流	$I_R(25^\circ\text{C})$ (100°C)	0.5 20			0.5 10	mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D	200				pF	$V_R=4\text{V},$ $f=1\text{MHz}$

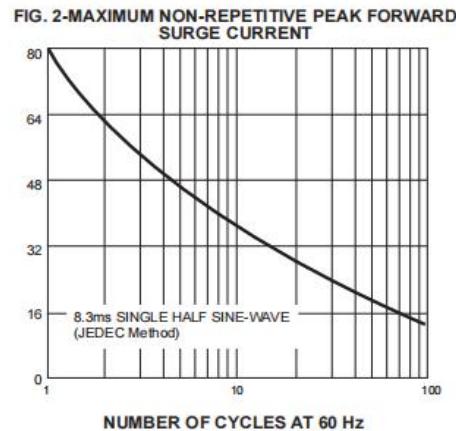
DSK32W-DSK310W

■ Typical Characteristic Curve 典型特性曲线

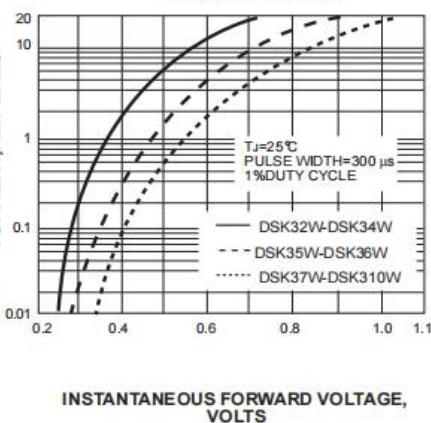
AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES



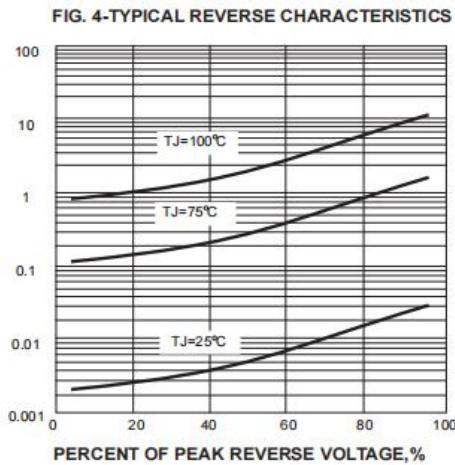
PEAK FORWARD SURGE CURRENT,
AMPERES



INSTANTANEOUS FORWARD
CURRENT, AMPERES



INSTANTANEOUS REVERSE CURRENT,
MILLIAMPERES



■ SOD-123FL Dimension 外形封装尺寸 Unit in millimeters 单位：毫米

